Renesas Electronics America Inc - R5F3651TNFC#U0 Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	32MHz
Connectivity	EBI/EMI, I²C, SIO, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	111
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	47K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	128-LQFP
Supplier Device Package	128-LFQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f3651tnfc-u0

1.3 Product List

Table 1.5 and Table 1.6 list product information. Figure 1.1 shows the Part No., with Memory Size and Package, and Figure 1.2 shows the Marking Diagram (Top View).

Table 1.5 Product List (1/2) As of July 2012

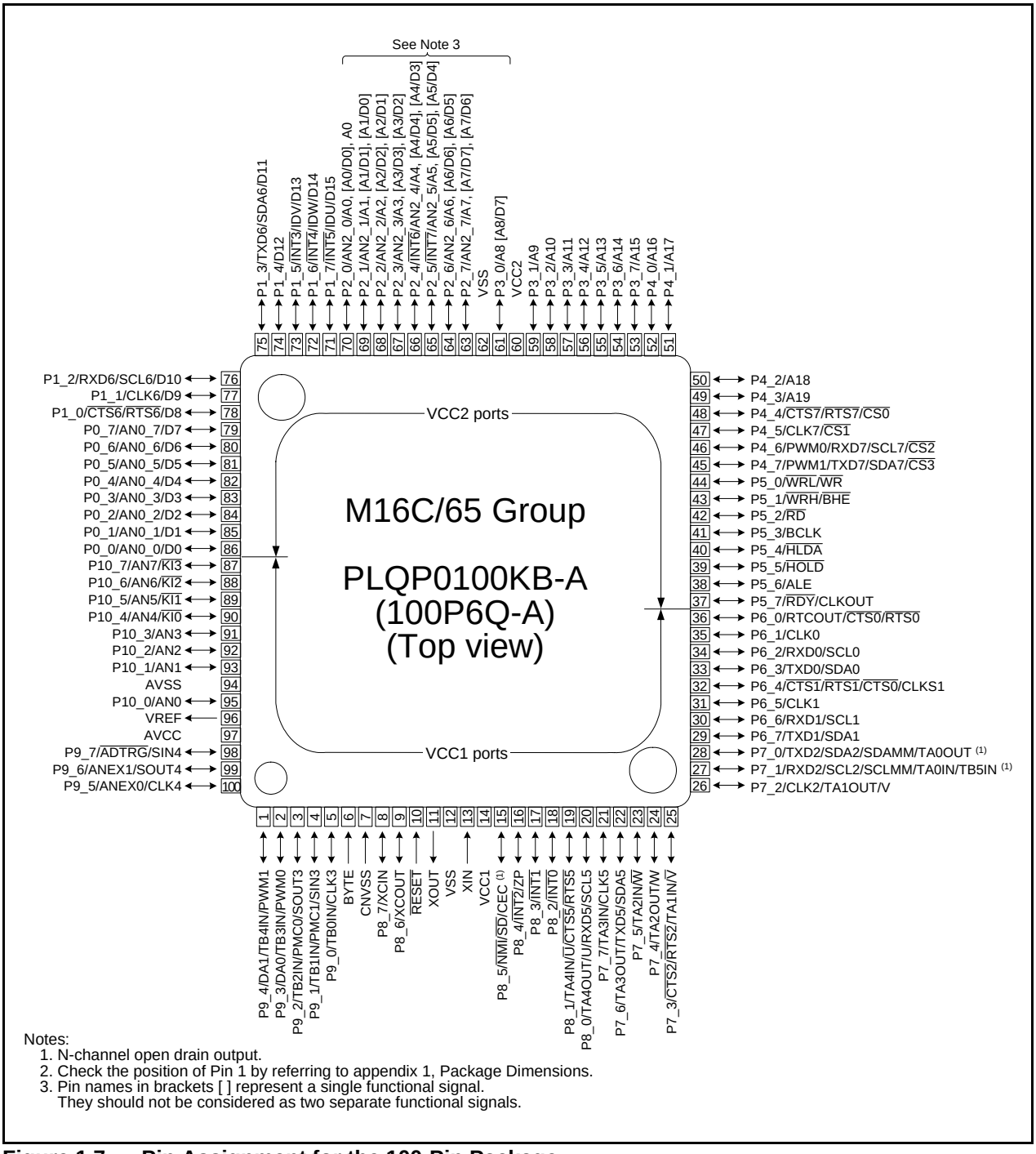
Part No.	ROM Capacity			RAM Capacity	Package Code	Remarks
	Program ROM 1	Program ROM 2	Data flash			
R5F36506NFA	128 KB	16 KB	4 KB × 2 blocks	12 KB	PRQP0100JD-B	Operating temperature -20°C to 85°C
R5F36506NFB					PLQP0100KB-A	
R5F36506DFA					PRQP0100JD-B	Operating temperature -40°C to 85°C
R5F36506DFB					PLQP0100KB-A	
R5F3651ENFC	256 KB	16 KB	4 KB × 2 blocks	20 KB	PLQP0128KB-A	Operating temperature -20°C to 85°C
R5F3650ENFA					PRQP0100JD-B	
R5F3650ENFB					PLQP0100KB-A	
R5F3651EDFC					PLQP0128KB-A	Operating temperature -40°C to 85°C
R5F3650EDFA					PRQP0100JD-B	
R5F3650EDFB					PLQP0100KB-A	
R5F3651KNFC	384 KB	16 KB	4 KB × 2 blocks	31 KB	PLQP0128KB-A	Operating temperature -20°C to 85°C
R5F3650KNFA					PRQP0100JD-B	
R5F3650KNFB					PLQP0100KB-A	
R5F3651KDFC					PLQP0128KB-A	Operating temperature -40°C to 85°C
R5F3650KDFA					PRQP0100JD-B	
R5F3650KDFB					PLQP0100KB-A	
R5F3651MNFC	512 KB	16 KB	4 KB × 2 blocks	31 KB	PLQP0128KB-A	Operating temperature -20°C to 85°C
R5F3650MNFA					PRQP0100JD-B	
R5F3650MNFB					PLQP0100KB-A	
R5F3651MDFC					PLQP0128KB-A	Operating temperature -40°C to 85°C
R5F3650MDFA					PRQP0100JD-B	
R5F3650MDFB					PLQP0100KB-A	
R5F3651NNFC	512 KB	16 KB	4 KB × 2 blocks	47 KB	PLQP0128KB-A	Operating temperature -20°C to 85°C
R5F3650NNFA					PRQP0100JD-B	
R5F3650NNFB					PLQP0100KB-A	
R5F3651NDFC					PLQP0128KB-A	Operating temperature -40°C to 85°C
R5F3650NDFA					PRQP0100JD-B	
R5F3650NDFB					PLQP0100KB-A	
R5F3651RNFC	640 KB	16 KB	4 KB × 2 blocks	47 KB	PLQP0128KB-A	Operating temperature -20°C to 85°C
R5F3650RNFA					PRQP0100JD-B	
R5F3650RNFB					PLQP0100KB-A	
R5F3651RDFC					PLQP0128KB-A	Operating temperature -40°C to 85°C
R5F3650RDFA					PRQP0100JD-B	
R5F3650RDFB					PLQP0100KB-A	

(D): Under development
(P): Planning

Previous package codes are as follows:
PLQP0128KB-A: 128P6Q-A
PRQP0100JD-B: 100P6F-A
PLQP0100KB-A: 100P6Q-A

Table 1.7 Pin Names for the 128-Pin Package (1/3)

Pin No.	Control Pin	Port	I/O Pin for Peripheral Function				Bus Control Pin
			Interrupt	Timer	Serial interface	A/D converter, D/A converter	
1	VREF						
2	AVCC						
3		P9_7			SIN4	$\overline{ADTRG}$	
4		P9_6			SOUT4	ANEX1	
5		P9_5			CLK4	ANEX0	
6		P9_4		TB4IN/PWM1		DA1	
7		P9_3		TB3IN/PWM0		DA0	
8		P9_2		TB2IN/PMC0	SOUT3		
9		P9_1		TB1IN/PMC1	SIN3		
10		P9_0		TB0IN	CLK3		
11		P14_1					
12		P14_0					
13	BYTE						
14	CNVSS						
15	XCIN	P8_7					
16	XCOUT	P8_6					
17	$\overline{RESET}$						
18	XOUT						
19	VSS						
20	XIN						
21	VCC1						
22		P8_5	$\overline{NMI}$	$\overline{SD}$	CEC		
23		P8_4	$\overline{INT2}$	ZP			
24		P8_3	$\overline{INT1}$				
25		P8_2	$\overline{INT0}$				
26		P8_1		TA4IN/$\overline{U}$	$\overline{CTS5}$/$\overline{RTS5}$		
27		P8_0		TA4OUT/U	RXD5/SCL5		
28		P7_7		TA3IN	CLK5		
29		P7_6		TA3OUT	TXD5/SDA5		
30		P7_5		TA2IN/$\overline{W}$			
31		P7_4		TA2OUT/W			
32		P7_3		TA1IN/$\overline{V}$	$\overline{CTS2}$/$\overline{RTS2}$		
33		P7_2		TA1OUT/V	CLK2		
34		P7_1		TA0IN/TB5IN	RXD2/SCL2/SCLMM		
35		P7_0		TA0OUT	TXD2/SDA2/SDAMM		
36		P6_7			TXD1/SDA1		
37	VCC1						
38		P6_6			RXD1/SCL1		
39	VSS						
40		P6_5			CLK1		
41		P6_4			$\overline{CTS1}$/$\overline{RTS1}$/$\overline{CTS0}$/CLKS1		
42		P6_3			TXD0/SDA0		
43		P6_2			RXD0/SCL0		
44		P6_1			CLK0		
45		P6_0		RTCOUT	$\overline{CTS0}$/$\overline{RTS0}$		
46		P13_7					
47		P13_6					
48		P13_5					
49		P13_4					
50	CLKOUT	P5_7					$\overline{RDY}$



Notes:
1. N-channel open drain output.
2. Check the position of Pin 1 by referring to appendix 1, Package Dimensions.
3. Pin names in brackets [ ] represent a single functional signal.
They should not be considered as two separate functional signals.

Figure 1.7 Pin Assignment for the 100-Pin Package

Table 1.13 Pin Functions for the 128-Pin Package (2/3)

Signal Name	Pin Name	I/O	Power Supply	Description
Main clock input	XIN	I	VCC1	I/O for the main clock oscillator. Connect a ceramic resonator or crystal between pins XIN and XOUT. (1) Input an external clock to XIN pin and leave XOUT pin open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O for a sub clock oscillator. Connect a crystal between pins XCIN and XCOUT. (1) Input an external clock to XCIN pin and leave XCOUT pin open.
Sub clock output	XCOUT	O	VCC1	
BCLK output	BCLK	O	VCC2	Outputs the BCLK signal.
Clock output	CLKOUT	O	VCC2	Outputs a clock with the same frequency as fC, f1, f8, or f32.
$\overline{INT}$ interrupt input	$\overline{INT0}$ to $\overline{INT2}$	I	VCC1	Input for the $\overline{INT}$ interrupt.
	$\overline{INT3}$ to $\overline{INT7}$	I	VCC2	
$\overline{NMI}$ interrupt input	$\overline{NMI}$	I	VCC1	Input for the $\overline{NMI}$ interrupt.
Key input interrupt input	$\overline{KI0}$ to $\overline{KI3}$	I	VCC1	Input for the key input interrupt.
Timer A	TA0OUT to TA4OUT	I/O	VCC1	I/O for timers A0 to A4 (TA0OUT is N-channel open drain output).
	TA0IN to TA4IN	I	VCC1	Input for timers A0 to A4.
	ZP	I	VCC1	Input for Z-phase.
Timer B	TB0IN to TB5IN	I	VCC1	Input for timers B0 to B5.
Three-phase motor control timer	U, $\overline{U}$, V, $\overline{V}$, W, $\overline{W}$	O	VCC1	Output for the three-phase motor control timer.
	$\overline{SD}$	I	VCC1	Forced cutoff input.
	IDU, IDV, IDW	I	VCC2	Input for the position data.
Real-time clock output	RTCOUT	O	VCC1	Output for the real-time clock.
PWM output	PWM0, PWM1	O	VCC1, VCC2	PWM output.
Remote control signal receiver input	PMC0, PMC1	I	VCC1	Input for the remote control signal receiver.
Serial interface UART0 to UART2, UART5 to UART7	$\overline{CTS0}$ to $\overline{CTS2}$, $\overline{CTS5}$	I	VCC1	Input pins to control data transmission.
	$\overline{CTS6}$, $\overline{CTS7}$	I	VCC2	
	$\overline{RTS0}$ to $\overline{RTS2}$, $\overline{RTS5}$	O	VCC1	Output pins to control data reception.
	$\overline{RTS6}$, $\overline{RTS7}$	O	VCC2	
	CLK0 to CLK2, CLK5	I/O	VCC1	Transmit/receive clock I/O.
	CLK6, CLK7	I/O	VCC2	
	RXD0 to RXD2, RXD5	I	VCC1	Serial data input.
	RXD6, RXD7	I	VCC2	
	TXD0 to TXD2, TXD5	O	VCC1	Serial data output. (2)
	TXD6, TXD7	O	VCC2	
	CLKS1	O	VCC1	Output for the transmit/receive clock multiple-pin output function.

Notes:
1. Contact the manufacturer of crystal/ceramic resonator regarding the oscillation characteristics.
2. TXD2, SDA2, and SCL2 are N-channel open drain output pins. TXDi (i = 0, 1, 5 to 7), SDAi, and SCLi can be selected as CMOS output pins or N-channel open drain output pins.

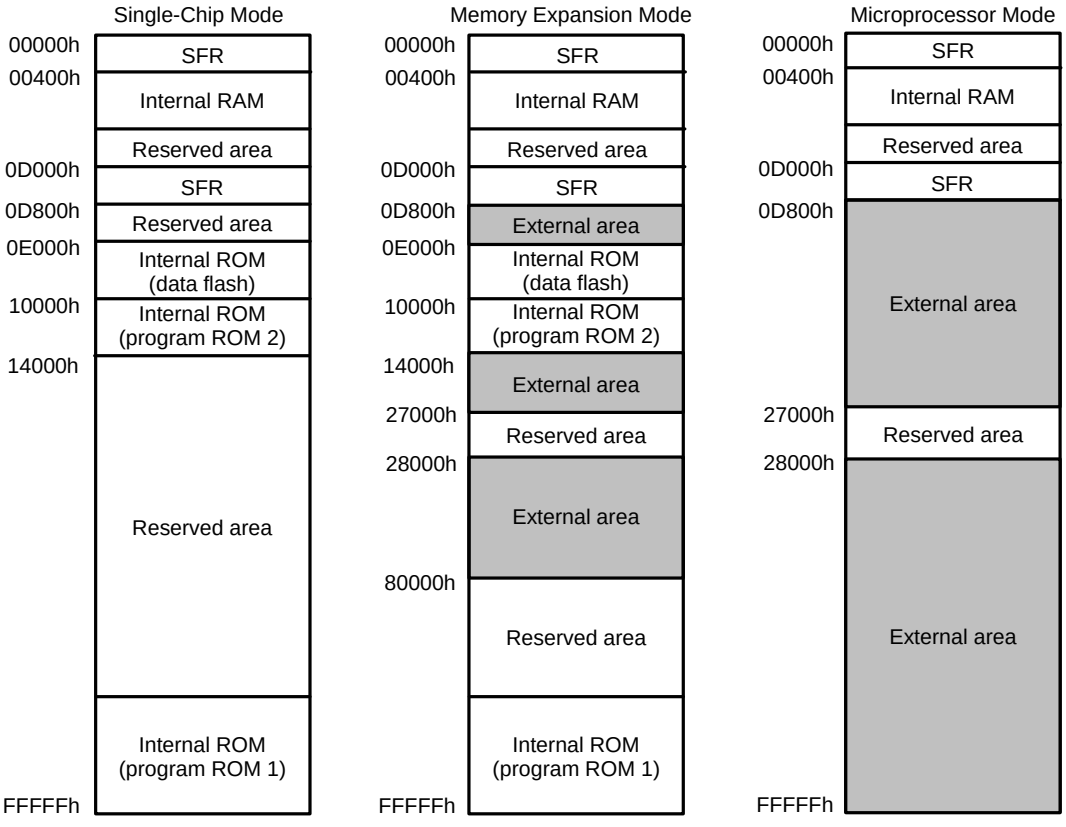
3.3 Accessible Area in Each Mode

Areas that can be accessed vary depending on processor mode and the status of each control bit. Figure 3.3 shows the Accessible Area in Each Mode.

In single-chip mode, the SFRs, internal RAM, and internal ROM can be accessed.

In memory expansion mode, the SFRs, internal RAM, internal ROM, and external areas can be accessed. Address space is expandable to 4 MB with the memory area expansion function.

In microprocessor mode, the SFRs, internal RAM, and external areas can be accessed. Address space is expandable to 4 MB with the memory area expansion function. Allocate ROM to the fixed vector table from FFFDCh to FFFFFh.



Notes:
1. Do not access reserved areas.
2. The figure above applies under the following conditions:
   Single-chip mode and memory expansion mode
   - The PM10 bit in the PM1 register is 1
     (addresses 0E000h to 0FFFFh are used as data flash)
   - The PRG2C0 bit in the PRG2C register is 0 (program ROM 2 enabled)
   - The PM13 bit in the PM1 register is 1
     (all areas in internal RAM, and the program ROM 1 area from 80000h are usable)
   - The IRON bit in the PRG2C register is 1
     (program ROM 1 in addresses 40000h to 7FFFFh enabled)

   Microprocessor mode
   - The PM10 bit is 0 (addresses 0E000h to 0FFFFh are used as the $\overline{CS2}$ area)
   - The PRG2C0 bit is 1 (program ROM 2 disabled)

Figure 3.3 Accessible Area in Each Mode

Table 4.7 SFR Information (7) (1)

Address	Register	Symbol	Reset Value
01E0h	Timer B3-1 Register	TB31	XXh
01E1h			XXh
01E2h	Timer B4-1 Register	TB41	XXh
01E3h			XXh
01E4h	Timer B5-1 Register	TB51	XXh
01E5h			XXh
01E6h	Pulse Period/Pulse Width Measurement Mode Function Select Register 2	PPWFS2	XXXX X000b
01E7h			
01E8h	Timer B Count Source Select Register 2	TBCS2	00h
01E9h	Timer B Count Source Select Register 3	TBCS3	X0h
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	PMC0 Function Select Register 0	PMC0CON0	00h
01F1h	PMC0 Function Select Register 1	PMC0CON1	00XX 0000b
01F2h	PMC0 Function Select Register 2	PMC0CON2	0000 00X0b
01F3h	PMC0 Function Select Register 3	PMC0CON3	00h
01F4h	PMC0 Status Register	PMC0STS	00h
01F5h	PMC0 Interrupt Source Select Register	PMC0INT	00h
01F6h	PMC0 Compare Control Register	PMC0CPC	XXX0 X000b
01F7h	PMC0 Compare Data Register	PMC0CPD	00h
01F8h	PMC1 Function Select Register 0	PMC1CON0	XXX0 X000b
01F9h	PMC1 Function Select Register 1	PMC1CON1	XXXX 0X00b
01FAh	PMC1 Function Select Register 2	PMC1CON2	0000 00X0b
01FBh	PMC1 Function Select Register 3	PMC1CON3	00h
01FCh	PMC1 Status Register	PMC1STS	X000 X00Xb
01FDh	PMC1 Interrupt Source Select Register	PMC1INT	X000 X00Xb
01FEh			
01FFh			
0200h			
0201h			
0202h			
0203h			
0204h			
0205h	Interrupt Source Select Register 3	IFSR3A	00h
0206h	Interrupt Source Select Register 2	IFSR2A	00h
0207h	Interrupt Source Select Register	IFSR	00h
0208h			
0209h			
020Ah			
020Bh			
020Ch			
020Dh			
020Eh	Address Match Interrupt Enable Register	AIER	XXXX XX00b
020Fh	Address Match Interrupt Enable Register 2	AIER2	XXXX XX00b

X: Undefined

Note:
1. The blank areas are reserved. No access is allowed.

4.2 Notes on SFRs

4.2.1 Register Settings

Table 4.19 lists Registers with Write-Only Bits and registers whose function differs between reading and writing. Set these registers with immediate values. Do not use read-modify-write instructions. When establishing the next value by altering the existing value, write the existing value to the RAM as well as to the register. Transfer the next value to the register after making changes in the RAM.
Read-modify-write instructions can be used when writing to the no register bits.

Table 4.19 Registers with Write-Only Bits

Address	Register	Symbol
0249h	UART0 Bit Rate Register	U0BRG
024Bh to 024Ah	UART0 Transmit Buffer Register	U0TB
0259h	UART1 Bit Rate Register	U1BRG
025Bh to 025Ah	UART1 Transmit Buffer Register	U1TB
0269h	UART2 Bit Rate Register	U2BRG
026Bh to 026Ah	UART2 Transmit Buffer Register	U2TB
0273h	SI/O3 Bit Rate Register	S3BRG
0277h	SI/O4 Bit Rate Register	S4BRG
0289h	UART5 Bit Rate Register	U5BRG
028Bh to 028Ah	UART5 Transmit Buffer Register	U5TB
0299h	UART6 Bit Rate Register	U6BRG
029Bh to 029Ah	UART6 Transmit Buffer Register	U6TB
02A9h	UART7 Bit Rate Register	U7BRG
02ABh to 02AAh	UART7 Transmit Buffer Register	U7TB
02B6h	I2C0 Control Register 1	S3D0
02B8h	I2C0 Status Register 0	S10
0303h to 0302h	Timer A1-1 Register	TA11
0305h to 0304h	Timer A2-1 Register	TA21
0307h to 0306h	Timer A4-1 Register	TA41
030Ah	Three-Phase Output Buffer Register 0	IDB0
030Bh	Three-Phase Output Buffer Register 1	IDB1
030Ch	Dead Time Timer	DTT
030Dh	Timer B2 Interrupt Generation Frequency Set Counter	ICTB2
0327h to 0326h	Timer A0 Register	TA0
0329h to 0328h	Timer A1 Register	TA1
032Bh to 032Ah	Timer A2 Register	TA2
032Dh to 032Ch	Timer A3 Register	TA3
032Fh to 032Eh	Timer A4 Register	TA4
037Dh	Watchdog Timer Refresh Register	WDTR
037Eh	Watchdog Timer Start Register	WDTS

5.1.6 Voltage Detector and Power Supply Circuit Electrical Characteristics

Table 5.11 Voltage Detector 0 Electrical Characteristics

The measurement condition is V_{CC1} = 2.7 to 5.5 V, T_{opr} = -20°C to 85°C/-40°C to 85°C, unless otherwise specified.

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (1)	When V_{CC1} is falling.	1.60	1.90	2.20	V
	Voltage detection level Vdet0_2 (1)	When V_{CC1} is falling.	2.55	2.85	3.15	V
-	Voltage detector 0 response time (3)	When V_{CC1} falls from 5 V to (Vdet0_0 - 0.1) V			200	µs
-	Voltage detector self power consumption	VC25 = 1, V_{CC1} = 5.0 V		1.8		µA
$t_{d(E-A)}$	Waiting time until voltage detector operation starts (2)				100	µs

Notes:
1. Select the voltage detection level with the VDSEL1 bit in the OFS1 address.
2. Necessary time until the voltage detector operates when setting to 1 again after setting the VC25 bit in the VCR2 register to 0.
3. Time from when passing the V_{det0} until when a voltage monitor 0 reset is generated.

Table 5.12 Voltage Detector 1 Electrical Characteristics

The measurement condition is V_{CC1} = 2.7 to 5.5 V, T_{opr} = -20°C to 85°C/-40°C to 85°C, unless otherwise specified.

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_6 (1)	When V_{CC1} is falling.	2.79	3.09	3.39	V
	Voltage detection level Vdet1_B (1)	When V_{CC1} is falling.	3.54	3.84	4.14	V
	Voltage detection level Vdet1_F (1)	When V_{CC1} is falling.	3.94	4.44	4.94	V
-	Hysteresis width when V_{CC1} of voltage detector 1 is rising			0.15		V
-	Voltage detector 1 response time (3)	When V_{CC1} falls from 5 V to (Vdet1_0 - 0.1) V			200	µs
-	Voltage detector self power consumption	VC26 = 1, V_{CC1} = 5.0 V		1.8		µA
$t_{d(E-A)}$	Waiting time until voltage detector operation starts (2)				100	µs

Notes:
1. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
2. Necessary time until the voltage detector operates when setting to 1 again after setting the VC26 bit in the VCR2 register to 0.
3. Time from when passing the V_{det1} until when a voltage monitor 1 reset is generated.

$V_{CC1} = V_{CC2} = 5\ V$

Table 5.21 Electrical Characteristics (3)

R5F36506NFA, R5F36506NFB, R5F36506DFA, R5F36506DFB, R5F3650ENFA, R5F3650ENFB, R5F3650EDFA, R5F3650EDFB

$V_{CC1} = V_{CC2} = 4.2$ to 5.5 V, $V_{SS} = 0$ V at $T_{opr} = -20°C$ to 85°C/−40°C to 85°C, $f_{(BCLK)} = 32$ MHz unless otherwise specified.

Symbol	Parameter	Measuring Condition		Standard			Unit
				Min.	Typ.	Max.	
R_{fXCIN}	Feedback resistance XCIN				8		MΩ
I_{CC}	Power supply current In single-chip, mode, the output pin are open and other pins are V_{SS}	High-speed mode	$f_{(BCLK)}$ = 32 MHz XIN = 4 MHz (square wave), PLL multiplied by 8 125 kHz on-chip oscillator stopped		24.0		mA
			$f_{(BCLK)}$ =32 MHz, A/D conversion XIN = 4 MHz (square wave), PLL multiplied by 8 125 kHz on-chip oscillator stopped		24.7		mA
			$f_{(BCLK)}$ = 20 MHz XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped		16.0		mA
		40 MHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator on, divide-by-4 ($f_{(BCLK)}$ = 10 MHz) 125 kHz on-chip oscillator stopped		17.0		mA
		125 kHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator stopped, 125 kHz on-chip oscillator on, no division FMR22 = 1 (slow read mode)		500.0		µA
		Low-power mode	$f_{(BCLK)}$ = 32 kHz In low-power mode FMR22 = FMR23 = 1 On flash memory (1)		160.0		µA
			$f_{(BCLK)}$ = 32 kHz In low-power mode On RAM (1)		45.0		µA
		Wait mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator on Peripheral clock operating T_{opr} = 25°C		20.0		µA
			$f_{(BCLK)}$ = 32 kHz (oscillation capacity High) 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock operating T_{opr} = 25°C		11.0		µA
			$f_{(BCLK)}$ = 32 kHz (oscillation capacity Low) 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock operating T_{opr} = 25°C		6.0		µA
		Stop mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock stopped T_{opr} = 25°C		1.7		µA
		During flash memory program	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 5.0 V		20.0		mA
		During flash memory erase	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 5.0 V		30.0		mA

Note:
1. This indicates the memory in which the program to be executed exists.

$V_{CC1} = V_{CC2} = 5\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

Table 5.30 Timer A Input (Two-Phase Pulse Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	800		ns
$t_{su(TAIN-TAOUT)}$	TAiOUT input setup time	200		ns
$t_{su(TAOUT-TAIN)}$	TAiIN input setup time	200		ns

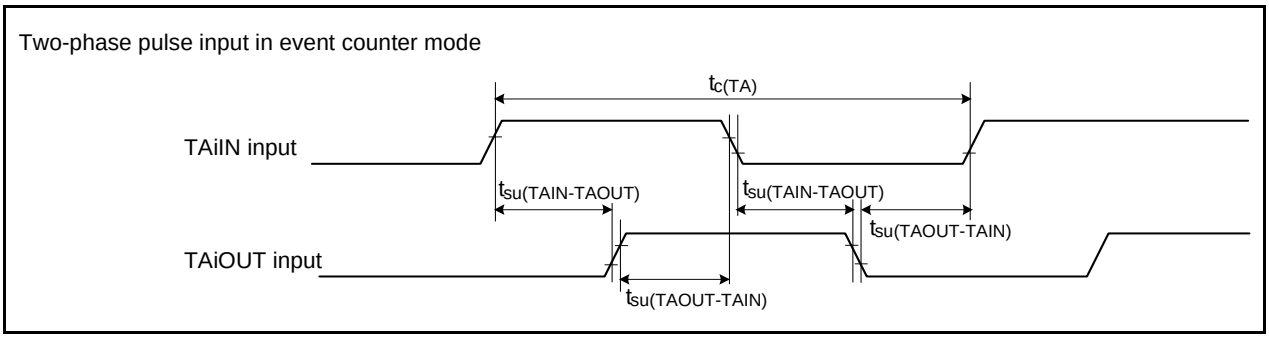


Figure 5.8 Timer A Input (Two-Phase Pulse Input in Event Counter Mode)

$V_{CC1} = V_{CC2} = 5\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.2.2.5 Serial Interface

Table 5.34 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200		ns
$t_{w(CKH)}$	CLKi input high pulse width	100		ns
$t_{w(CKL)}$	CLKi input low pulse width	100		ns
$t_{d(C-Q)}$	TXDi output delay time		80	ns
$t_{h(C-Q)}$	TXDi hold time	0		ns
$t_{su(D-C)}$	RXDi input setup time	70		ns
$t_{h(C-D)}$	RXDi input hold time	90		ns

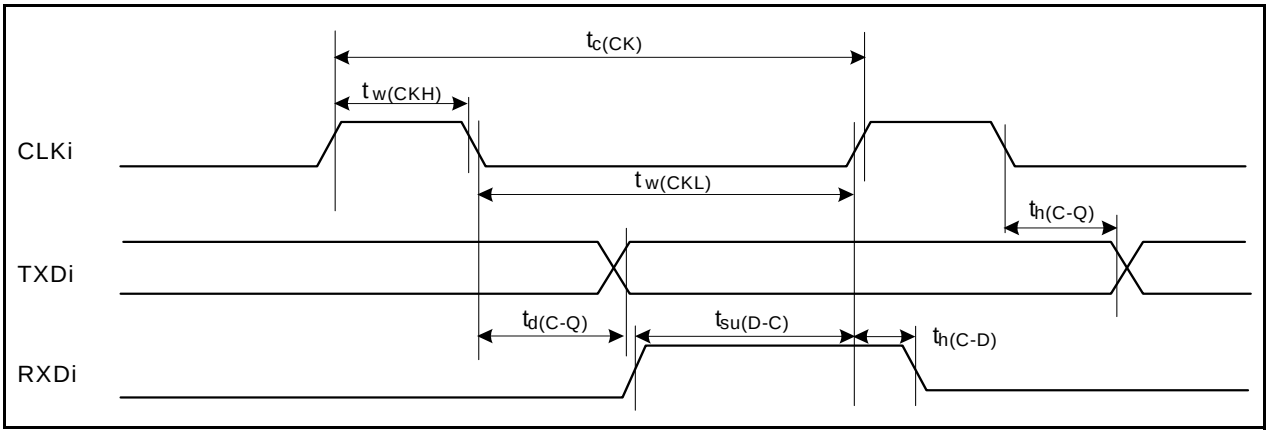


Figure 5.10 Serial Interface

5.2.2.6 External Interrupt $\overline{INTi}$ Input

Table 5.35 External Interrupt $\overline{INTi}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input high pulse width	250		ns
$t_{w(INL)}$	$\overline{INTi}$ input low pulse width	250		ns

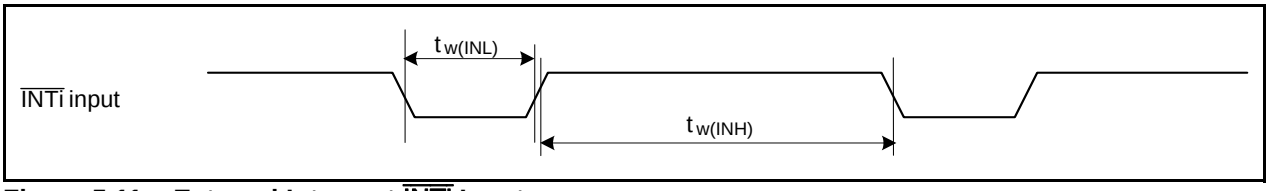


Figure 5.11 External Interrupt $\overline{INTi}$ Input

$V_{CC1} = V_{CC2} = 5\ V$

Switching Characteristics

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.2.4.3 In 2 or 3 Waits Setting, and When Accessing External Area and Using Multiplexed Bus

Table 5.40 Memory Expansion Mode and Microprocessor Mode (in 2 or 3 Waits Setting, and When Accessing External Area and Using Multiplexed Bus) (5)

Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.14		25	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		(Note 1)		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			25	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{h(RD-CS)}$	Chip select output hold time (in relation to RD)		(Note 1)		ns
$t_{h(WR-CS)}$	Chip select output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			25	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			25	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data output hold time (in relation to BCLK)		0		ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 2)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR)		(Note 1)		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time (in relation to BCLK)			15	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time (in relation to BCLK)		–4		ns
$t_{d(AD-ALE)}$	ALE signal output delay time (in relation to Address)		(Note 3)		ns
$t_{h(AD-ALE)}$	ALE signal output hold time (in relation to Address)		(Note 4)		ns
$t_{d(AD-RD)}$	RD signal output delay from the end of address		0		ns
$t_{d(AD-WR)}$	WR signal output delay from the end of address		0		ns
$t_{dz(RD-AD)}$	Address output floating start time			8	ns

Notes:

1. Calculated according to the BCLK frequency as follows:
$$\frac{0.5 \times 10^9}{f_{(BCLK)}} - 10[ns]$$
2. Calculated according to the BCLK frequency as follows:
$$\frac{(n - 0.5) \times 10^9}{f_{(BCLK)}} - 40[ns]$$
n is 2 for 2-wait setting, 3 for 3-wait setting.
3. Calculated according to the BCLK frequency as follows:
$$\frac{0.5 \times 10^9}{f_{(BCLK)}} - 25[ns]$$
4. Calculated according to the BCLK frequency as follows:
$$\frac{0.5 \times 10^9}{f_{(BCLK)}} - 15[ns]$$
5. When using multiplex bus, set $f_{(BCLK)}$ 12.5 MHz or less.

$V_{CC1} = V_{CC2} = 3\ V$

Table 5.46 Electrical Characteristics (4)

R5F3651RNFC, R5F3650RNFA, R5F3650RNFB, R5F3651RDFC, R5F3650RDFA, R5F3650RDFB, R5F3651TNFC, R5F3650TNFA, R5F3650TNFB, R5F3651TDFC, R5F3650TDFA, R5F3650TDFB

$V_{CC1} = V_{CC2} = 2.7$ to $3.3\ V$, $V_{SS} = 0\ V$ at $T_{opr} = -20°C$ to $85°C$/$-40°C$ to $85°C$, $f_{(BCLK)} = 32$ MHz unless otherwise specified.

Symbol	Parameter	Measuring Condition		Standard			Unit
				Min.	Typ.	Max.	
R_{fXCIN}	Feedback resistance XCIN				25		MΩ
I_{CC}	Power supply current In single-chip, mode, the output pin are open and other pins are V_{SS}	High-speed mode	$f_{(BCLK)}$ = 32 MHz XIN = 4 MHz (square wave), PLL multiplied by 8 125 kHz on-chip oscillator stopped		32.0		mA
			$f_{(BCLK)}$ = 32 MHz, A/D conversion XIN = 4 MHz (square wave), PLL multiplied by 8 125 kHz on-chip oscillator stopped		32.7		mA
			$f_{(BCLK)}$ = 20 MHz XIN = 20 MHz (square wave) 125 kHz on-chip oscillator stopped		21.0		mA
		40 MHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator on, divide-by-4 (f(BCLK) = 10 MHz) 125 kHz on-chip oscillator stopped		23.0		mA
		125 kHz on-chip oscillator mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator on, no division FMR22 = 1 (slow read mode)		750.0		µA
		Low-power mode	$f_{(BCLK)}$ = 32 MHz In low-power mode, FMR 22 = FMR23 = 1 on flash memory (1)		300.0		µA
			$f_{(BCLK)}$ = 32 MHz In low-power mode, on RAM (1)		40.0		µA
		Wait mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator on Peripheral clock operating T_{opr} = 25°C		20.0		µA
			$f_{(BCLK)}$ = 32 MHz (oscillation capacity High) 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock operating T_{opr} = 25°C		8.0		µA
			$f_{(BCLK)}$ = 32 kHz (oscillation capacity Low) 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock operating T_{opr} = 25°C		4.0		µA
		Stop mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock stopped T_{opr} = 25°C		1.6		µA
		During flash memory program	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 3.0 V		20.0		mA
		During flash memory erase	$f_{(BCLK)}$ = 10 MHz, PM17 = 1 (one wait) V_{CC1} = 3.0 V		30.0		mA

Note:

1. This indicates the memory in which the program to be executed exists.

$V_{CC1} = V_{CC2} = 3\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 3$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.3.2.5 Serial Interface

Table 5.57 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300		ns
$t_{w(CKH)}$	CLKi input high pulse width	150		ns
$t_{w(CKL)}$	CLKi input low pulse width	150		ns
$t_{d(C-Q)}$	TXDi output delay time		160	ns
$t_{h(C-Q)}$	TXDi hold time	0		ns
$t_{su(D-C)}$	RXDi input setup time	100		ns
$t_{h(C-D)}$	RXDi input hold time	90		ns

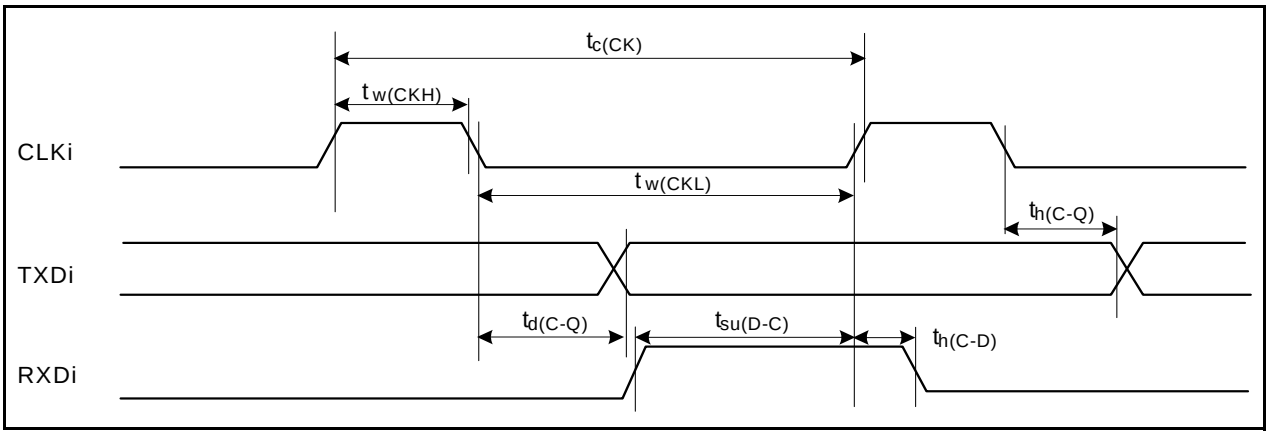


Figure 5.25 Serial Interface

5.3.2.6 External Interrupt $\overline{INTi}$ Input

Table 5.58 External Interrupt $\overline{INTi}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input high pulse width	380		ns
$t_{w(INL)}$	$\overline{INTi}$ input low pulse width	380		ns

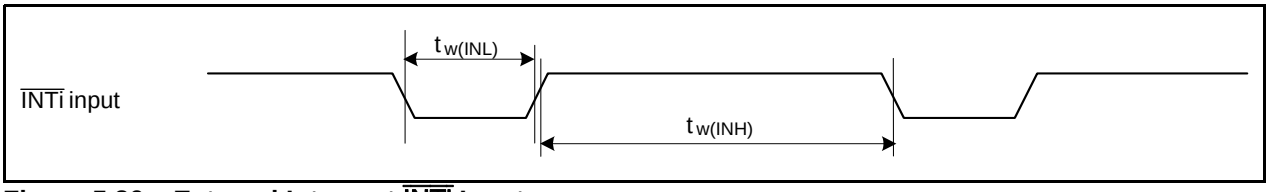


Figure 5.26 External Interrupt $\overline{INTi}$ Input

$V_{CC1} = V_{CC2} = 3\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 3$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.3.2.7 Multi-master I²C-bus

Table 5.59 Multi-master I²C-bus

Symbol	Parameter	Standard Clock Mode		Fast-mode		Unit
		Min.	Max.	Min.	Max.	
t_{BUF}	Bus free time	4.7		1.3		µs
$t_{HD;STA}$	Hold time in start condition	4.0		0.6		µs
t_{LOW}	Hold time in SCL clock 0 status	4.7		1.3		µs
t_R	SCL, SDA signals' rising time		1000	20 + 0.1 Cb	300	ns
$t_{HD;DAT}$	Data hold time	0		0	0.9	µs
t_{HIGH}	Hold time in SCL clock 1 status	4.0		0.6		µs
f_F	SCL, SDA signals' falling time		300	20 + 0.1 Cb	300	ns
$t_{su;DAT}$	Data setup time	250		100		ns
$t_{su;STA}$	Setup time in restart condition	4.7		0.6		µs
$t_{su;STO}$	Stop condition setup time	4.0		0.6		µs

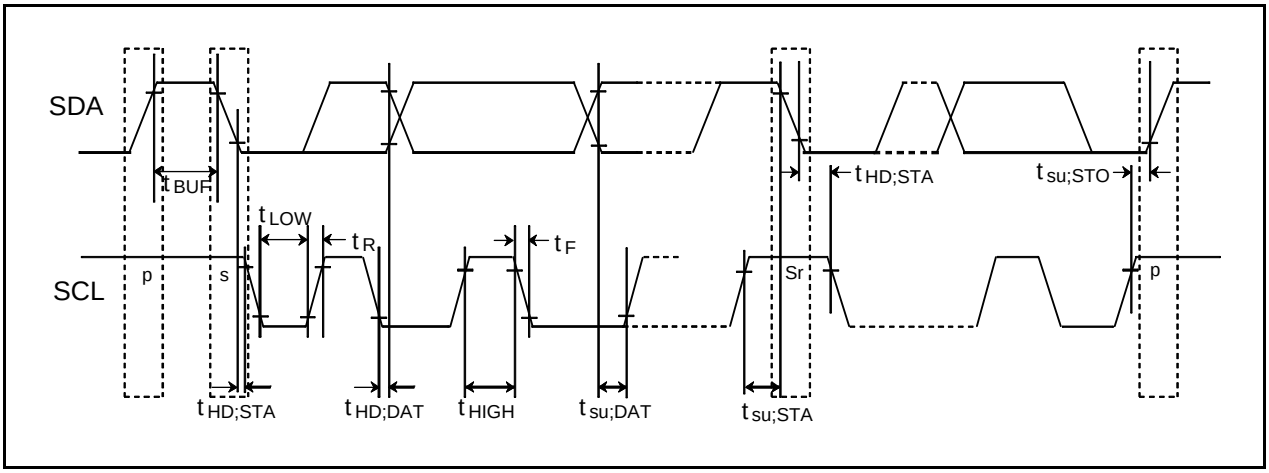


Figure 5.27 Multi-master I²C-bus

$V_{CC1} = V_{CC2} = 3\ V$

Switching Characteristics

($V_{CC1} = V_{CC2} = 3$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.3.4.2 In 1 to 3 Waits Setting and When Accessing External Area

Table 5.62 Memory Expansion Mode and Microprocessor Mode (in 1 to 3 Waits Setting and When Accessing External Area)

Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.29		30	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 2)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			30	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			25	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		-4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			30	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			30	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data output hold time (in relation to BCLK) (3)		0		ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 1)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR) (3)		(Note 2)		ns

Notes:

1. Calculated according to the BCLK frequency as follows:

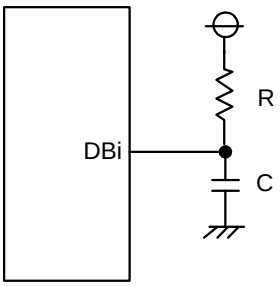
$$\frac{(n-0.5)\times 10^9}{f_{(BCLK)}} - 40[ns]$$

n is 1 for 1 wait setting, 2 for 2 waits setting and 3 for 3 waits setting.
When n = 1, $f_{(BCLK)}$ is 12.5 MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times 10^9}{f_{(BCLK)}} - 10[ns]$$

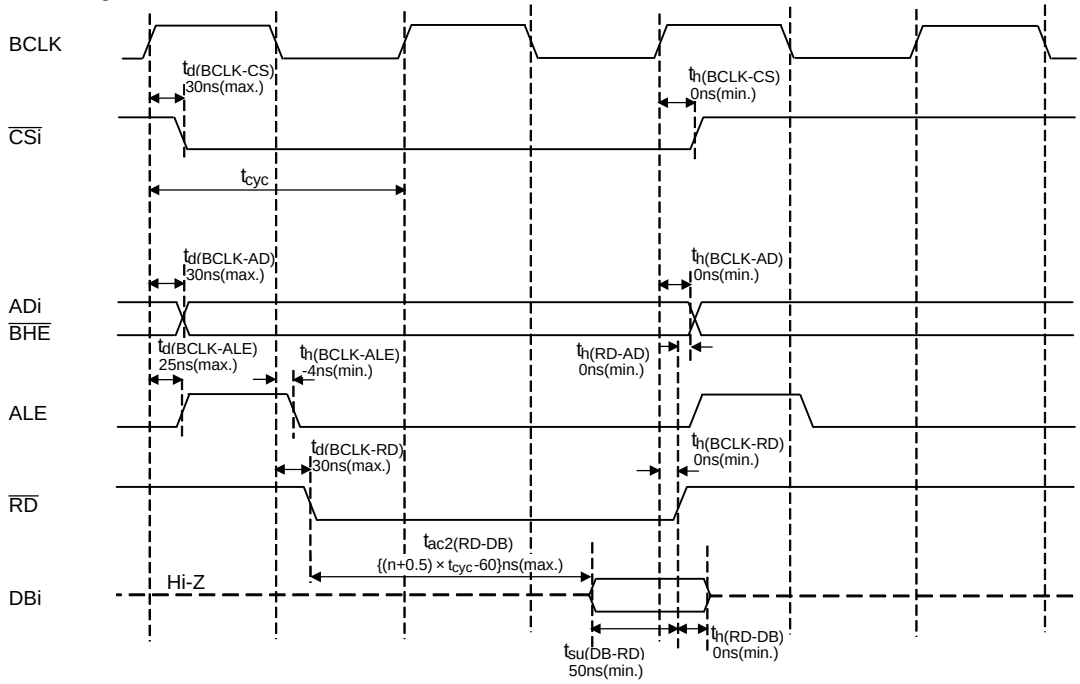
3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = -CR \times \ln(1 - V_{OL}/V_{CC2})$
by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC2}$, C = 30 pF, R = 1 kΩ, hold time of output low level is
$t = -30\ pF \times 1\ k\Omega \times \ln(1 - 0.2V_{CC2}/V_{CC2})$
= 6.7 ns.



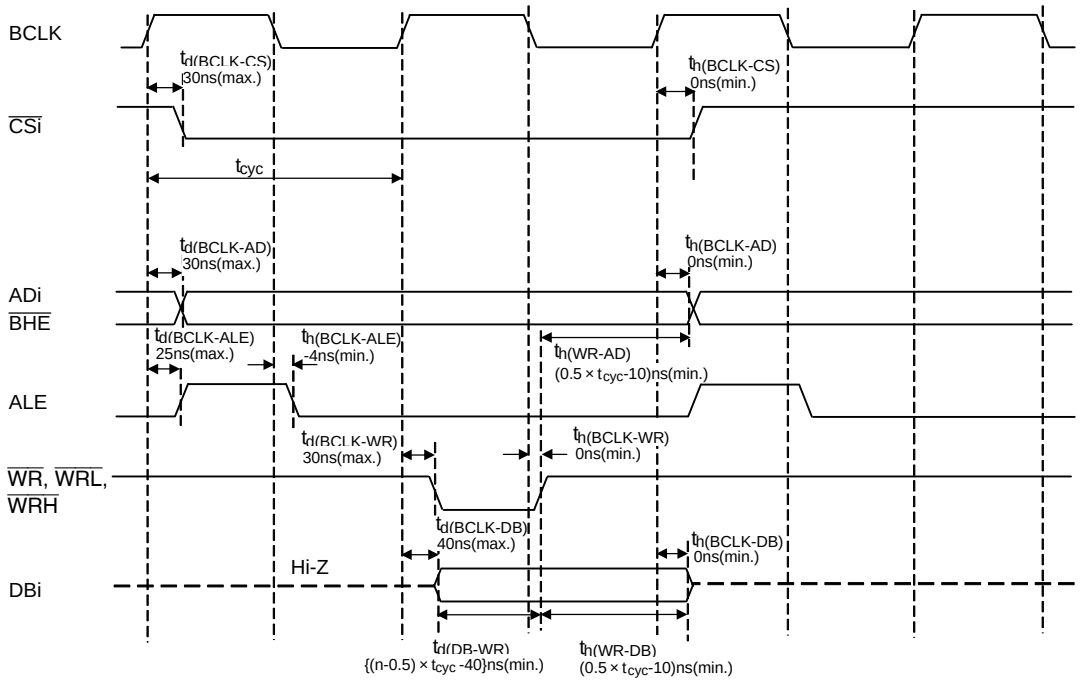
Memory Expansion Mode and Microprocessor Mode
(in 1 to 3 waits setting and when accessing external area)

$V_{CC1} = V_{CC2} = 3V$

Read timing



Write timing



$$t_{cyc} = \frac{1}{f_{(BCLK)}}$$

Measuring conditions

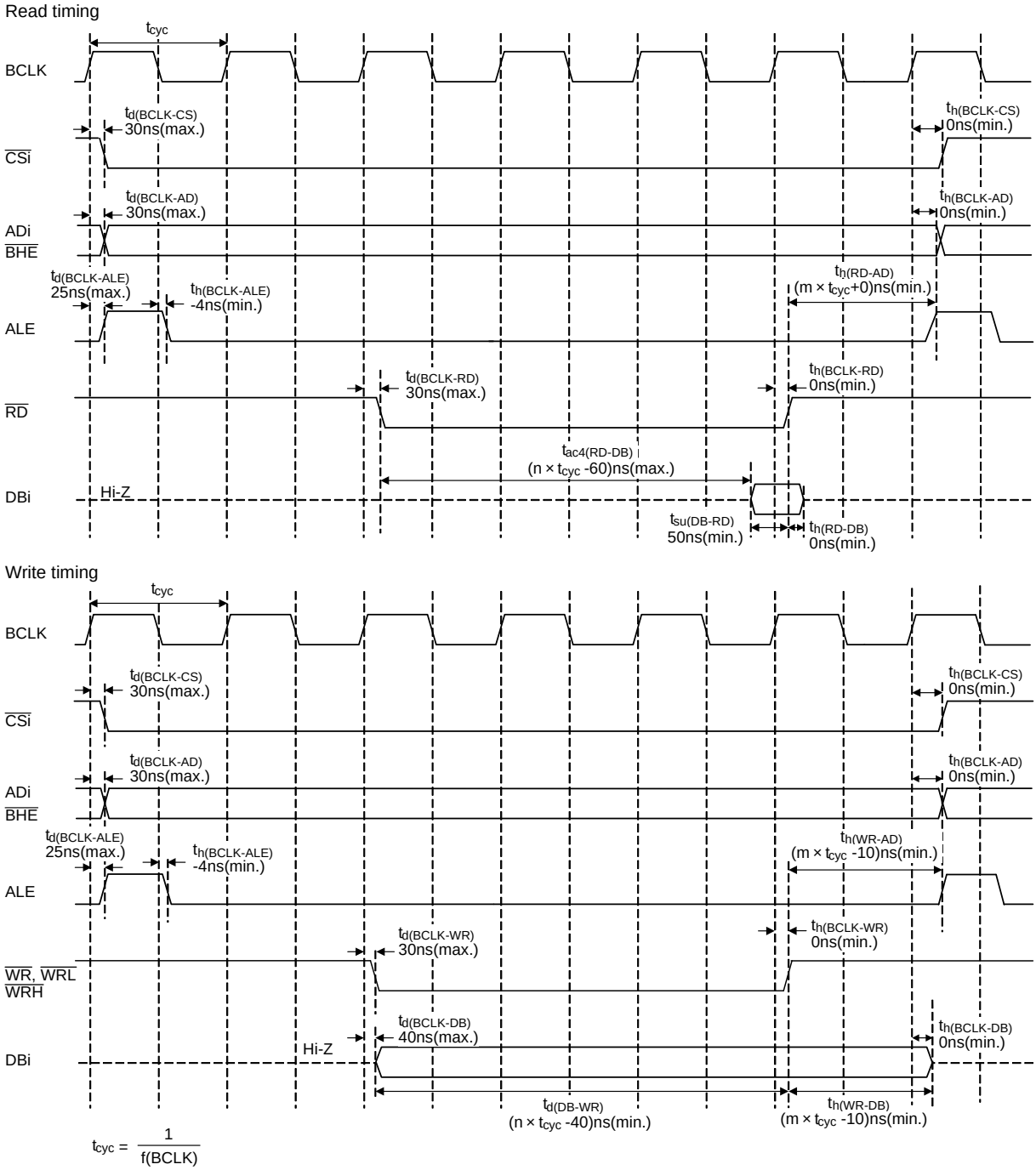
- $V_{CC1} = V_{CC2} = 3V$
- Input timing voltage: $V_{IL} = 0.6$ V, $V_{IH} = 2.4$ V
- Output timing voltage: $V_{OL} = 1.5$ V, $V_{OH} = 1.5$ V

n: 1 (when 1 wait)
2 (when 2 waits)
3 (when 3 waits)

Figure 5.31 Timing Diagram

Memory Expansion Mode and Microprocessor Mode
(in wait state setting 2 ϕ + 3 ϕ, 2 ϕ + 4 ϕ, 3ϕ + 4 ϕ, and 4 ϕ + 5 ϕ, and
when inserting 1 to 3 recovery cycles inserted and accessing external area)

$V_{CC1} = V_{CC2} = 3V$



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions

- $V_{CC1} = V_{CC2} = 3V$
- Input timing voltage: $V_{IL} = 0.6$ V, $V_{IH} = 2.4$ V
- Output timing voltage: $V_{OL} = 1.5$ V, $V_{OH} = 1.5$ V

n: 3 (when 2 ϕ + 3 ϕ)
4 (when 2 ϕ + 4 ϕ or 3 ϕ + 4 ϕ)
5 (when 4 ϕ + 5 ϕ)

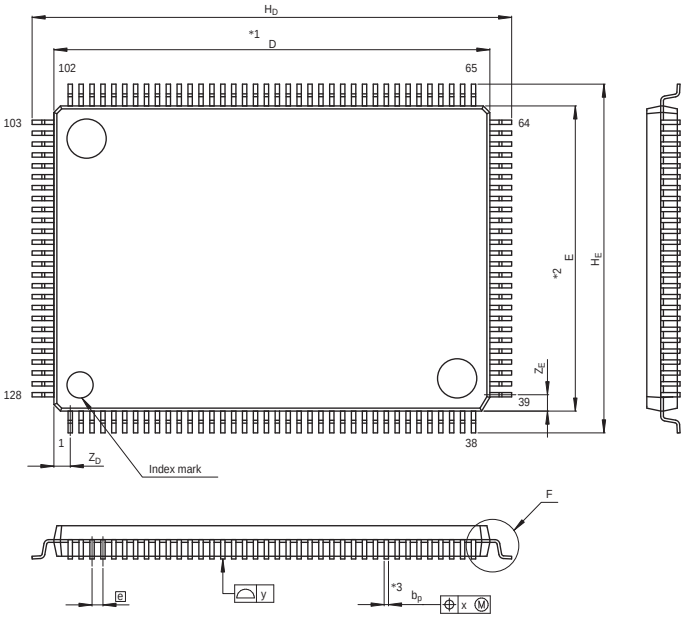
m: 1 (when 1 recovery cycle inserted)
2 (when 2 recovery cycles inserted)
3 (when 3 recovery cycles inserted)

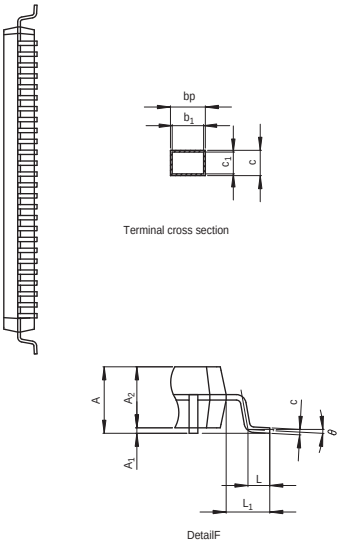
Figure 5.34 Timing Diagram

Appendix 1. Package Dimensions

The information on the latest package dimensions or packaging may be obtained from “Packages“ on the Renesas Electronics website.

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP128-14x20-0.50	PLQP0128KB-A	128P6Q-A	0.9g

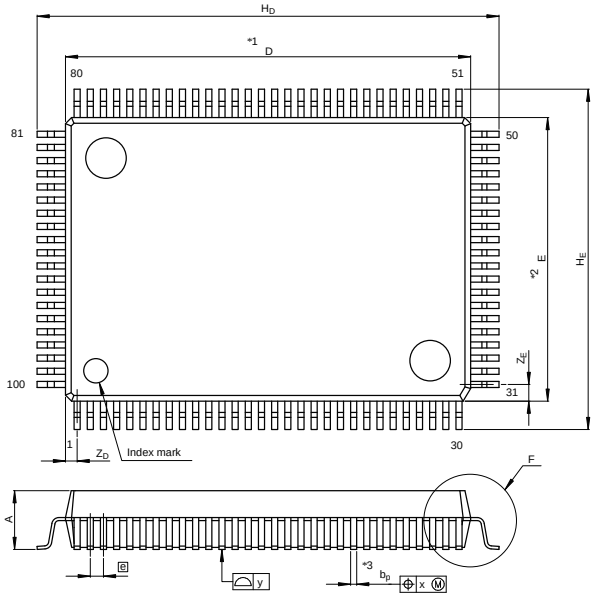


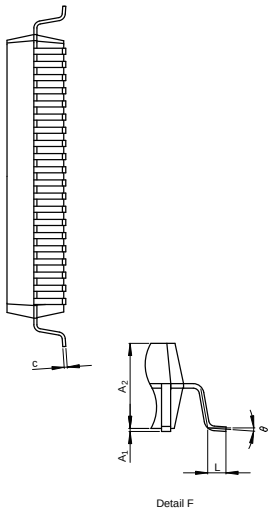


NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.9	20.0	20.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	21.8	22.0	22.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.125	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.10
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-QFP100-14x20-0.65	PRQP0100JD-B	100P6F-A	1.8g





NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	19.8	20.0	20.2
E	13.8	14.0	14.2
A_2	—	2.8	—
H_D	22.5	22.8	23.1
H_E	16.5	16.8	17.1
A	—	—	3.05
A_1	0	0.1	0.2
b_p	0.25	0.3	0.4
c	0.13	0.15	0.2
θ	0°	—	10°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
Z_D	—	0.575	—
Z_E	—	0.825	—
L	0.4	0.6	0.8

REVISION HISTORY	M16C/65 Group Datasheet

Rev.	Date	Description	
		Page	Summary
2.00	Dec 10, 2010	**Special Function Registers (SFRs)**	
		31	Table 4.1 SFR Information (1): • Deleted “the VCR1 register, the VCR2 register” from note 2. • Deleted notes 5 to 6 and added note 5.
		32	Table 4.2 SFR Information (2): Deleted notes 2 to 7 and added note 2.
		49	4.2.1 Register Settings: Added the description regarding read-modify-write instructions.
		50	Table 4.20 Read-Modify-Write Instructions: Added.
		Electrical Characteristics	
		51	Table 5.1 Absolute Maximum Ratings: Added a row for the data area value to T_{opr} (Flash program erase).
		52	Table 5.2 Recommended Operating Conditions (1/3): Added rows for the CEC value to V_{CC1}, V_{CC2}, V_{IH}, and V_{IL}.
		57	Table 5.9 Flash Memory (Program ROM 1, 2) Electrical Characteristics: Added a condition to the Read voltage row.
		60	Table 5.14 Power-On Reset Circuit: • Added the $t_{w(por)}$ row. • Added the last line in note 1.
		60	Figure 5.3 Power-On Reset Circuit Electrical Characteristics: Deleted note 2.
		64	Table 5.20 Electrical Characteristics (2): Added “ZP, IDU, IDV, IDW” to the V_{T+} - V_{T-} row.
		65	Table 5.21 Electrical Characteristics (3): Moved R5F3651ENFC and R5F3651EDFC to Table 5.22 Electrical Characteristics (4).
		73, 96	5.2.2.7 and 5.3.2.7 Multi-master I^2C-bus: Added.
		74 to 81, 97 to 104	Table 5.37 to Table 5.42 and Table 5.60 to Table 5.65 Memory Expansion Mode and Microprocessor Mode: Deleted the following: • $\overline{HOLD}$ input setup time • $\overline{HOLD}$ input hold time • $\overline{HLDA}$ output delay time
		74	Table 5.37 Memory Expansion Mode and Microprocessor Mode: Changed $\overline{RDY}$ input setup time from 30.
		75, 98	Figure 5.13 and Figure 5.28 Timing Diagram: Deleted lower figure (Common to wait state and no wait state settings).
		86, 109	Figure 5.19 and Figure 5.34 Timing Diagram: Changed the width of th(RD-AD).
		87	Table 5.43 Electrical Characteristics (1): • Added rows for the CEC value to V_{OL}, V_{T+}-V_{T-}, and Leakage current in powered-off state. • Added “ZP, IDU, IDV, IDW” to the V_{T+} - V_{T-} row.
		88	Table 5.44 Electrical Characteristics (2): Moved R5F3651ENFC and R5F3651EDFC to Table 5.45 Electrical Characteristics (3).
		88 to 90	Table 5.44 to Table 5.46 Electrical Characteristics (2) to (4): Changed “VCC1 = 5.0 V” to "VCC1 = 3.0 V" in the During flash memory program and During flash memory erase rows.
		97	Table 5.60 Memory Expansion Mode and Microprocessor Mode: Changed $\overline{RDY}$ input setup time from 40.
2.10	Ju. 31, 2012	**Electrical Characteristics**	
		Vcc = 5 V	
		65, 66, 67	Table 5.21 Electrical Characteristics (3), Table 5.22 Electrical Characteristics (4), and Table 5.23 Electrical Characteristics (5): Changed the Measuring Condition column of 40 MHz on-chip oscillator for the 40 MHz on-chip oscillator mode in the I_{CC}.
		Vcc = 3 V	
		88, 89, 90	Table 5.44 Electrical Characteristics (2), Table 5.45 Electrical Characteristics (3), and Table 5.46 Electrical Characteristics (4): Changed the Measuring Condition column of 40 MHz on-chip oscillator for the 40 MHz on-chip oscillator mode in the I_{CC}.